Time-over-threshold (TOT) studies with the DPTS

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Task list for DPTS studies

Laboratory measurements

| Task | Assigned | Timeframe | Details |
|--|--------------|------------|--|
| Power consumption study | Trieste/CERN | 24th April | Investigate the performance of the chip as a function of IBIAS. Look into the threshold, noise, FHR, ToT, and ToA. Also, investigate optimal working points for low IBIAS values. Only needed for VBB = -1.2 V |
| 2e15, 5e15 and 1e16 chips | CERN | ? | Investigate if the chips work: do at lower temp (< 15°C) and higher IRESET (> 70 pA), commission controlled environment setup |
| Bent DPTS | Trieste | ? | With WP4 investigate bent DPTS chips |
| Pixel-to-pixel variation in threshold and leakage current | Trieste | ? | See variations in chip biases pixel-to-pixel when all pixels are tuned to the same threshold |
| Study ToT pixel-to-pixel variation | ? | ? | What is the reason for such a large ToT RMS and pixel-to-pixel variation? Correlate the difference with other parameters |
| Remeasure all plots in paper with different chips | ? | ? | Remeasure all threshold, FHR and ToT dependence as well as Fe55 spectra shown in the paper for different chips |
| Pulsing capacitance measurement | ? | ? | Look at chip-to-chip and pixel-to-pixel variations |
| FHR and thermal noise study | ? | ? | Investigate sources of FHR: thermal, telegraph. Hot pixels. Chip-to-chip study |
| Dead pixels | ? | ? | Study pixels unresponsive to pulsing and external stimuli. |
| Power consumption | ? | ? | Study the chip performance at different power consumption levels |
| Characterise the CML | ORNL | ? | Performance as a function of BBIAS current |
| Regularly measure TID chips | CERN | Ongoing | Look into annealing effects on the chips: threshold, noise, noise occ, PID/GID clusters |
| Test different splits | ? | ? | Study the behaviour of different splits |
| Injecting noise via vbb or pwell | ? | ? | Study the chip behaviour with different noise levels |
| Separating PWELL and SUB | ? | ? | Study the chip behaviour with separate PWELL and SUB |
| Look at chip-to-chip variations | ? | ? | Study the chip-to-chip behaviour of currents, thresholds, noise and leakage current |
| DPTS timing back-to-back | CERN | ? | Use Sr90 to investigate the timing of two DPTS chips back-to-back (on hold for now, needs supplement with a testbeam measurement) |

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What is a good way to characterize this variation?



measurements at a given injected charge (V_H). The y error bar shown is the standard deviation of those 25 ^{5/26/2023} measurements. It is not the standard error of the mean.



Comparison of slope for all pixels



Next steps

- 1. Think about what are the best 'figure of merits' to use to characterize the pixel-to-pixel variation.
- 2. Take data with a wider range of injected charge. So far, I only go up to $V_{\rm H}$ = 300 mV.
- 3. Repeat the TOT vs. injected charge scans for other voltage and current settings. Need to figure out how to automate the process a bit.